

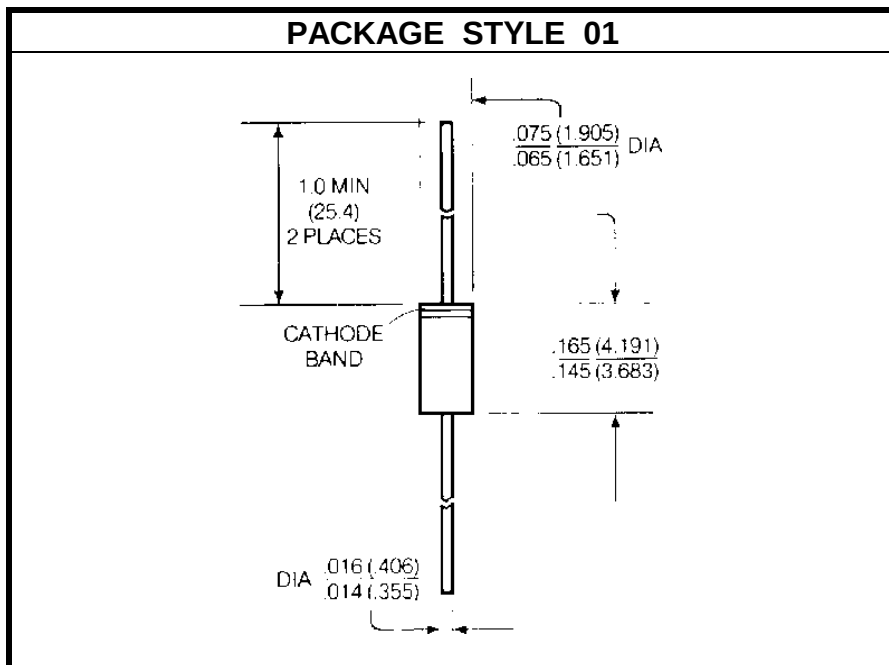
SILICON PIN DIODE CHIP

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I_F	100 mA
V_R	300 V
P_{DISS}	250 mW @ $T_A = 25^\circ\text{C}$
θ_{JC}	20°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10 \mu\text{A}$	300			V
C_J	$V_R = 50 \text{ V}$ $V_R = 40 \text{ V}$			0.2	pF
R_S	$I_F = 50 \text{ mA}$ $f = 100 \text{ MHz}$			0.6	Ohms
T_L	$I_F = 10 \text{ mA}$ $I_R = 6.0 \text{ mA}$		1000		nS
T_{rr}	$I_F = 20 \text{ mA}$ $I_R = 100 \text{ mA}$		100		nS